



### PNP PRE-BIASED SMALL SIGNAL DUAL SURFACE MOUNT TRANSISTOR

### **Features**

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDC)
- Built-In Biasing Resistors
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

P/N	R1 (NOM)	R2 (NOM)
DDA124EH	22kΩ	22kΩ
DDA144EH	47kΩ	47kΩ
DDA143EH	4.7kΩ	4.7kΩ
DDA114YH	10kΩ	47kΩ
DDA123JH	2.2kΩ	47kΩ
DDA114EH	10kΩ	10kΩ
DDA143TH	4.7kΩ	_
DDA114TH	10kΩ	_

## **Mechanical Data**

Case: SOT563

Case Material: Molded Plastic UL Flammability Classification

Rating 94V-0

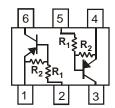
Moisture Sensitivity: Level 1 per J-STD-020

Terminals: Finish – Matte Tin Annealed over Copper Leadframe.

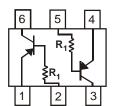
Solderable per MIL-STD-202, Method 208 @3

- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

### SCHEMATIC DIAGRAM, TOP VIEW



R<sub>1</sub>, R<sub>2</sub> Device Schematic



R<sub>1</sub> Only Device Schematic

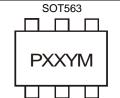
## **Ordering Information** (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DDA124EH-7	AEC-Q101	P17	7	8	3,000
DDA144EH-7	AEC-Q101	P20	7	8	3,000
DDA143EH-7	AEC-Q101	P08	7	8	3,000
DDA114YH-7	AEC-Q101	P14	7	8	3,000
DDA123JH-7	AEC-Q101	P06	7	8	3,000
DDA114EH-7	AEC-Q101	P13	7	8	3,000
DDA143TH-7	AEC-Q101	P07	7	8	3,000
DDA114TH-7	AEC-Q101	P12	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



PXX = Product Type Marking Code YM = Date Code Marking Y = Year ex: C = 2015 M = Month ex: 9 = September

Date Code Key

Year	2015	2016	20	)17	2018	2019	2020	2021	20	22	2023	2024
Code	С	D		E	F	G	Н	- 1	,	J	K	L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# 

Characteristic		Symbol	Value	Unit
Supply Voltage		Vcc	-50	V
Input Voltage	DDA124EH DDA144EH DDA143EH DDA114YH DDA123JH DDA114EH DDA143TH DDA114TH	V <sub>IN</sub>	+10 to -40 +10 to -40 +10 to -30 +6 to -40 +5 to -12 +10 to -40 +5V Max +5V Max	V
Output Current	DDA124EH DDA144EH DDA143EH DDA114YH DDA123JH DDA114EH DDA143TH DDA114TH	lo	-30 -30 -100 -70 -100 -50 -100	mA
Output Current	All	I <sub>C</sub> (Max)	-100	mA
Power Dissipation		P <sub>D</sub>	150	mW
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Note: 5. Mounted on FR4 Board with recommended pad layout at http://www.diodes.com/package-outlines.html.



# Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

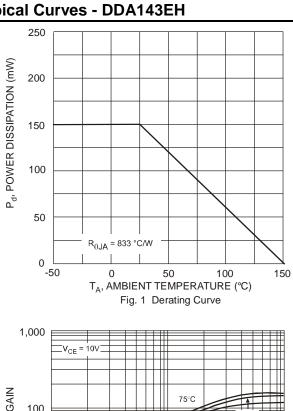
Characteristic (DDA143TH & DDA114TH only)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	_	_	V	I <sub>C</sub> = -50μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-50		_	٧	I <sub>C</sub> = -1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	_	_	V	I <sub>E</sub> = -50μA
Collector Cut-Off Current	I <sub>CBO</sub>	_	_	-0.5	μΑ	V <sub>CB</sub> = -50V
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	-0.5	μΑ	V <sub>EB</sub> = -4V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>			-0.3	V	$I_C/I_B = -2.5 \text{mA} / -0.25 \text{mA}$ DDA143TH $I_C/I_B = -1 \text{mA} / -0.1 \text{mA}$ DDA114TH
DC Current Transfer Ratio	h <sub>FE</sub>	100	250	600		I <sub>C</sub> = -1mA, V <sub>CE</sub> = -5V
Gain-Bandwidth Product*	f <sub>T</sub>		250	_	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz

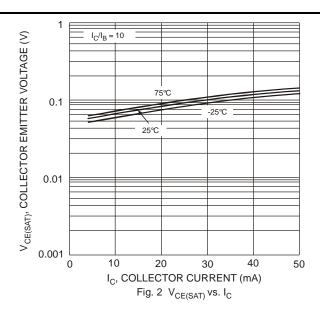
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
	DDA124EH DDA144EH DDA143EH DDA114YH DDA123JH DDA114EH	V <sub>L(OFF)</sub>	-0.5 -0.5 -0.5 -0.3 -0.5 -0.5	-1.1 -1.1 -1.1 — — -1.1	—	V	$V_{CC} = -5V$ , $I_{O} = -100\mu A$
Input Voltage	DDA124EH DDA144EH DDA143EH DDA114YH DDA123JH DDA114EH	$V_{L(ON)}$		-1.9 -1.9 -1.9 — — —	-3.0 -3.0 -3.0 -1.4 -1.1 -3.0		V <sub>O</sub> = -0.3V, I <sub>O</sub> = -5mA V <sub>O</sub> = -0.3V, I <sub>O</sub> = -2mA V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA V <sub>O</sub> = -0.3V, I <sub>O</sub> = -1mA V <sub>O</sub> = -0.3V, I <sub>O</sub> = -5mA V <sub>O</sub> = -0.3V, I <sub>O</sub> = -10mA
Output Voltage	DDA124EH DDA144EH DDA143EH DDA114YH DDA123JH DDA114EH	V <sub>O(ON)</sub>		-0.1	-0.3	V	I <sub>O</sub> /I <sub>L</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>L</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>L</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>L</sub> = -5mA / -0.25mA I <sub>O</sub> /I <sub>L</sub> = -5mA / -0.25mA I <sub>O</sub> /I <sub>L</sub> = -10mA / -0.5mA
Input Current	DDA124EH DDA144EH DDA143EH DDA114YH DDA123JH DDA114EH	lι	_	_	-0.36 -0.18 -1.8 -0.88 -3.6 -0.88	mA	V <sub>I</sub> = -5V
Output Current		I <sub>O(OFF)</sub>	_	_	-0.5	μΑ	$V_{CC} = -50V, V_{I} = -0V$
DC Current Gain	DDA124EH DDA144EH DDA143EH DDA114YH DDA123JH DDA114EH	GL	56 68 20 68 80 30	_	_	_	$V_O = -5V$ , $I_O = -5mA$ $V_O = -5V$ , $I_O = -5mA$ $V_O = -5V$ , $I_O = -10mA$ $V_O = -5V$ , $I_O = -10mA$ $V_O = -5V$ , $I_O = -10mA$ $V_O = -5V$ , $I_O = -5mA$
Gain-Bandwidth Product*		f⊤	_	250	_	MHz	$V_{CE} = -10V, I_{E} = -5mA, f = 100MHz$

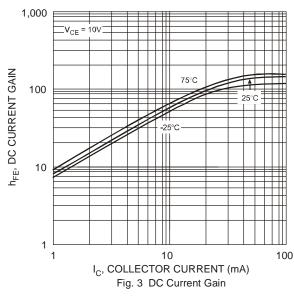
<sup>\*</sup> Transistor - For Reference Only

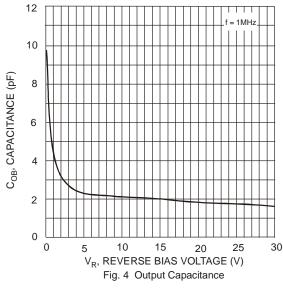


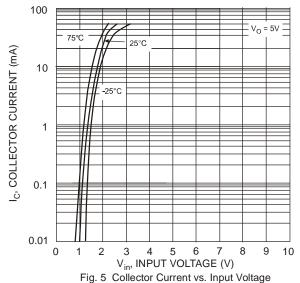
## **Typical Curves - DDA143EH**

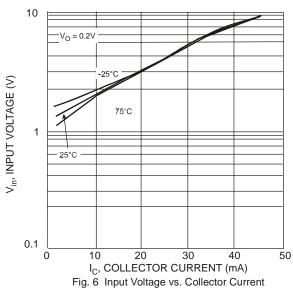










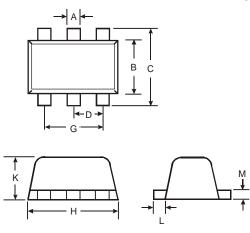




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT563**

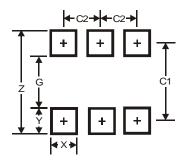


	SOT563							
Dim	Min	Max	Тур					
Α	0.15	0.30	0.20					
В	1.10	1.25	1.20					
С	1.55	1.70	1.60					
D	-	-	0.50					
G	0.90	1.10	1.00					
Н	1.50	1.70	1.60					
K	0.55	0.60	0.60					
L	0.10	0.30	0.20					
M	0.10	0.18	0.11					
All	Dimens	sions in	mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT563



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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